

APPENDIX A

VERSION WITH MARKINGS TO SHOW CHANGES MADE IN THE SPECIFICATION

On page 7, the paragraph starting at line 17 is amended as follows:

In this embodiment, the CCD imaging apparatus is constructed so that a part of a gate 12B of the gate 12 which is not related to charge readout (i.e., barrier gate 12B) is cut in a slanted line form from a corner of the photodiode portion 1 to the vertical CCD portion 3, as opposed to the gate portion 2 of Figs. 4A and 4B, whereby the width $L_{2.5}$ or W_4 of a gate portion 12a of a readout gate 12A adjacent to the photodiode portion 1 is widened up to the same width as that of the photodiode portion 1 and the width $L_{2.4}$ or W_4 of a gate portion 12b of the readout gate 12A and the gate length $l_{1.4}$ at the vertical CCD portion 3 side is unchanged ($l_{1.4} = l_{1.1}$).

On page 8, the paragraph starting at line 9 is amended as follows:

The CCD imaging apparatus employs two types of gates, gate portions 12A and 12B. One of them is a gate used during charge readout (read-out gate 12A), placed below the former (barrier gate 12B). In a portion where the two gates (read-out gate 12A and barrier gate 12B) overlap, the barrier gate 12B or the gate not related to readout is dominant.

On page 8, the paragraph starting at line 15 is amended as follows:

The embodiment is characterized in that the barrier gate 12B or a gate not related to charge readout is cut in a slanted line form as described above the width $L_{2.5}$ or W_4 of the readout gate portion 12a adjacent to the photodiode portion 1 is widened, so that an electric field applied to that portion is intensified during activation so that charges within the photodiode portion 1 can be easily read out.